# MBR1635, MBR1645, MBRB1645, NRVBB1645

# Switch-mode Power Rectifiers

16 A, 35 and 45 V

These state-of-the-art devices use the Schottky Barrier principle with a platinum barrier metal.

#### **Features**

- Guard-ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Weight: 1.9 Grams for TO-220
  - 1.7 Grams for D<sup>2</sup>PAK
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR1635 MBR1645 MBRB1645	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	35 45 45	V
Average Rectified Forward Current Delay (Rated V <sub>R</sub> , T <sub>C</sub> = 163°C) Total Device	I <sub>F(AV)</sub>	16	Α
Peak Repetitive Forward Current, Per Leg (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 157°C) Total Device	I <sub>FRM</sub>	32	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	150	Α
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I <sub>RRM</sub>	1.0	Α
Storage Temperature Range	T <sub>stg</sub>	-65 to +175	°C
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000	V/μs

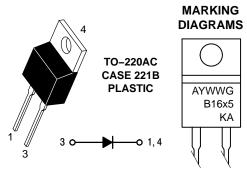
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta,JA}$ .



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= Assembly Location

Y = Year

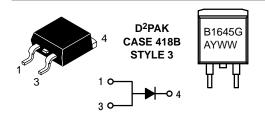
WW = Work Week

B16x5 = Device Code

x = 3 or 4

KA = Diode Polarity

G = Pb-Free Package



B1645 = Device Code A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

### **ORDERING INFORMATION**

Device	Package	Shipping		
MBR1635G	TO-220 (Pb-Free)	50 Units / Rail		
MBR1645G	TO-220 (Pb-Free)	50 Units / Rail		
MBRB1645T4G	D <sup>2</sup> PAK (Pb-Free)	800 Units / Rail		
NRVBB1645T4G	D <sup>2</sup> PAK (Pb-Free)	800 Units / Rail		

## MBR1635, MBR1645, MBRB1645, NRVBB1645

### THERMAL CHARACTERISTICS

Characteristic		Symbol	Value	Unit
Maximum Thermal Resistance,	Junction-to-Case	$R_{ heta JC}$	1.5	°C/W

### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 16 \text{ Amps}, T_C = 125^{\circ}\text{C}$ ) ( $i_F = 16 \text{ Amps}, T_C = 25^{\circ}\text{C}$ )	VF	0.57 0.63	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}C$ ) (Rated dc Voltage, $T_C = 25^{\circ}C$ )	i <sub>R</sub>	40 0.2	mA

<sup>2.</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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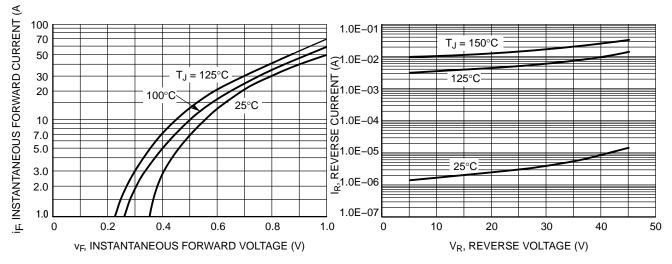


Figure 1. Typical Forward Voltage

**Figure 2. Typical Reverse Current** 

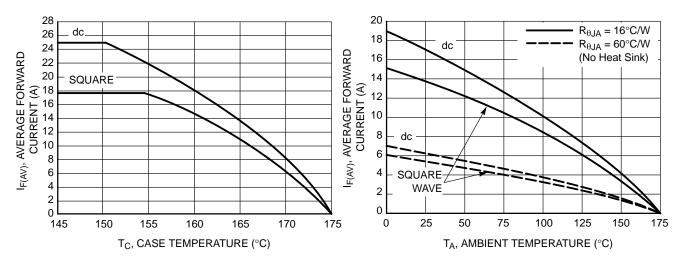


Figure 3. Current Derating, Case, Per Leg

Figure 4. Current Derating, Ambient

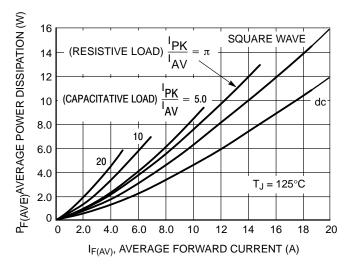


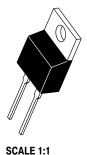
Figure 5. Forward Power Dissipation

# **MECHANICAL CASE OUTLINE**

Q

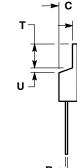
**PACKAGE DIMENSIONS** 





TO-220, 2-LEAD CASE 221B-04 **ISSUE F** 

**DATE 12 APR 2013** 



## NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

PIN 1. ANODE 2. N/A 3. CATHODE

4. ANODE

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# **MECHANICAL CASE OUTLINE**

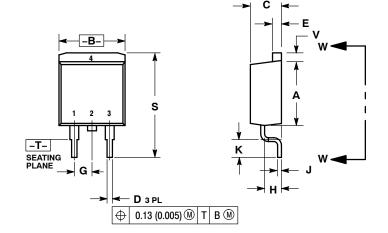




D<sup>2</sup>PAK 3 CASE 418B-04 **ISSUE L** 

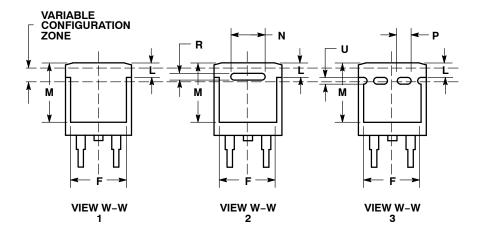
**DATE 17 FEB 2015** 

### SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INC	HES	MILLIM	IETERS
ым	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00	REF
Р	0.079 REF		2.00 REF	
R	0.039 REF		0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

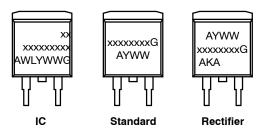
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# GENERIC MARKING DIAGRAM\*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

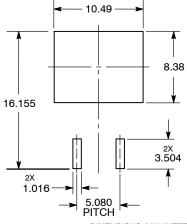
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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